November 2013



SGH40N60UF 600 V PT IGBT

General Description

Fairchild's UF series IGBTs provide low conduction and switching losses. UF series is designed for the applications such as general inverter and PFC where high speed switching is required feature.

Features

- High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)} = 2.1 \text{ V} @ I_C = 20 \text{ A}$
- High Input Impedance

Application

· General Inverter, PFC





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		600	V
V _{GES}	Gate-Emitter Voltage		± 20	V
	Collector Current	$@ T_C = 25^{\circ}C$	40	А
IC	Collector Current	@ T _C = 100°C	20	А
I _{CM (1)}	Pulsed Collector Current		160	А
P _D	Maximum Power Dissipation	@ T _C = 25°C	160	W
	Maximum Power Dissipation	@ T _C = 100°C	64	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.77	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V, } I_{C} = 250 \text{ uA}$	600			V
ΔB _{VCES} / ΔΤ _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA		0.6		V/°C
CES	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V			250	uA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0 V$			± 100	nA
On Cha	racteristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 20 \text{ mA}, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
	Collector to Emitter	$I_C = 20 \text{ A}, V_{GE} = 15 \text{ V}$		2.1	2.6	V
V _{CE(sat)}	Saturation Voltage	$I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}$		2.6		V
Dynami	c Characteristics					
C _{ies}	Input Capacitance	V 99.V.V 9.V		1430		pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$ $f = 1 \text{ MHz}$		170		pF
C _{res}	Reverse Transfer Capacitance			50		pF
Switchii	ng Characteristics Turn-On Delay Time			15		ns
r (OII)	Rise Time			30		ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, I_{C} = 20 \text{ A},$		65		
t _f	Fall Time				130	
•		$R_{G} = 10 \Omega$, $V_{GF} = 15 V$.			130 150	ns
Eon	Turn-On Switching Loss	$R_G = 10 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 25^{\circ}C$		50 160		
E _{off}				50	150	ns ns
E _{off}	Turn-On Switching Loss			50 160	150	ns ns uJ
E _{off}	Turn-On Switching Loss Turn-Off Switching Loss			50 160 200	150	ns ns uJ uJ
E _{off} E _{ts}	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss			50 160 200 360	150 600	ns ns uJ uJ
E _{off} E _{ts} cd(on)	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time			50 160 200 360 30	150 600 	ns ns uJ uJ uJ ns
E _{off} E _{ts} t _{d(on)} t _r	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time	Inductive Load, T _C = 25°C	 	50 160 200 360 30 37	150 600 	ns ns uJ uJ uJ ns
E _{off} E _{ts} d(on) cr d(off)	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time	Inductive Load, $T_C = 25$ °C $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$	 	50 160 200 360 30 37 110	150 600 200	ns ns uJ uJ uJ ns ns
E _{off} E _{ts} td(on) tr td(off) tf	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time	Inductive Load, $T_C = 25$ °C $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V,}$	 	50 160 200 360 30 37 110 144	150 600 200	ns ns uJ uJ uJ ns ns ns
E _{off} E _{ts} t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss	Inductive Load, $T_C = 25$ °C $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V,}$	 	50 160 200 360 30 37 110 144 310	150 600 200 250	ns ns uJ uJ ns ns ns us uJ uJ
E _{off} Ets td(on) tr td(off) tf Eon Eoff Ets	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V,}$ Inductive Load, $T_C = 125^{\circ}C$	 	50 160 200 360 30 37 110 144 310 430	150 600 200 250 	ns ns uJ uJ ns ns ns ns ns uJ
Eon Eoff Ets td(on) tr td(off) tf Eon Eoff Eog Qg	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss	Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V,}$ Inductive Load, $T_C = 125^{\circ}C$ $V_{CE} = 300 \text{ V, } I_C = 20 \text{ A,}$	 	50 160 200 360 30 37 110 144 310 430 740	150 600 200 250 1200	ns uJ uJ ns ns ns ns ns uL uJ
E _{off} Ets td(on) tr td(off) tt Eon Eoff Ets	Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss Total Switching Loss Total Gate Charge	Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300 \text{ V, } I_C = 20 \text{ A,}$ $R_G = 10 \Omega, V_{GE} = 15 \text{ V,}$ Inductive Load, $T_C = 125^{\circ}C$	 	50 160 200 360 30 37 110 144 310 430 740 97	150 600 200 250 1200 150	ns ns uJ uJ ns ns ns us uJ nc

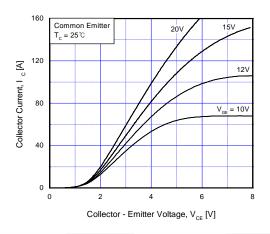
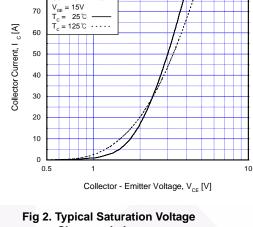


Fig 1. Typical Output Characteristics



80

Common Emitter

Characteristics

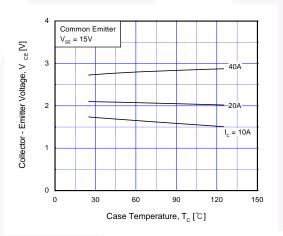


Fig 3. Saturation Voltage vs. Case **Temperature at Variant Current Level**

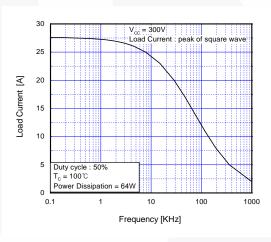


Fig 4. Load Current vs. Frequency

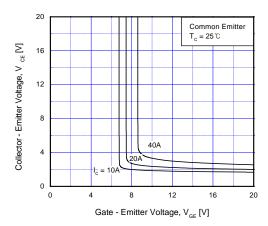


Fig 5. Saturation Voltage vs. V_{GE}

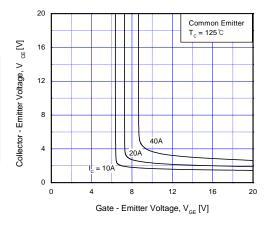


Fig 6. Saturation Voltage vs. V_{GE}

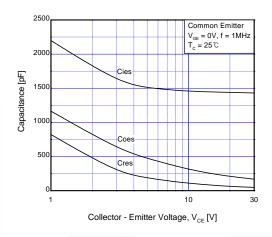


Fig 7. Capacitance Characteristics

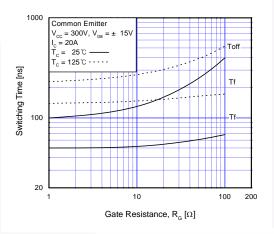


Fig 9. Turn-Off Characteristics vs.
Gate Resistance

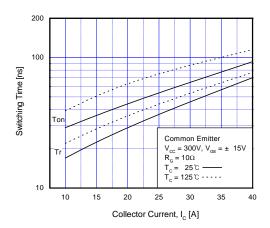


Fig 11. Turn-On Characteristics vs. Collector Current

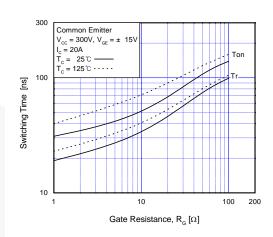


Fig 8. Turn-On Characteristics vs.
Gate Resistance

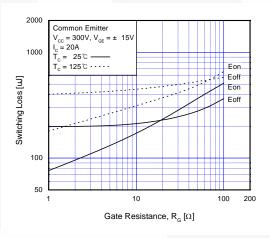


Fig 10. Switching Loss vs. Gate Resistance

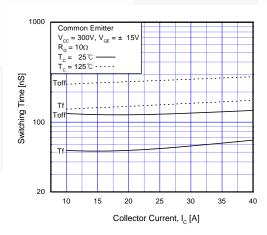


Fig 12. Turn-Off Characteristics vs. Collector Current

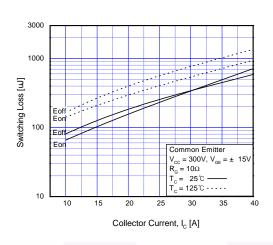


Fig 13. Switching Loss vs. Collector Current

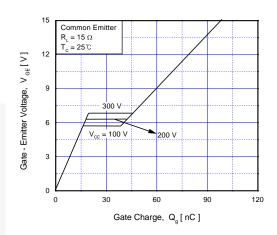


Fig 14. Gate Charge Characteristics

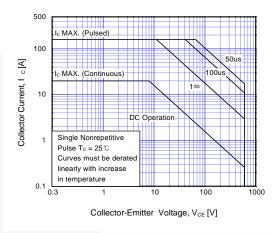


Fig 15. SOA Characteristics

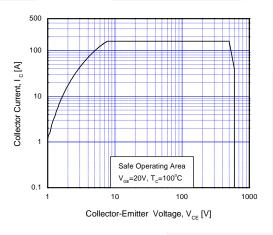


Fig 16. Turn-Off SOA Characteristics

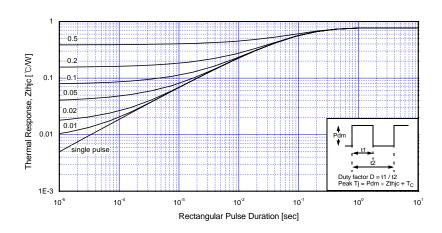


Fig 17. Transient Thermal Impedance of IGBT

Mechanical Dimensions

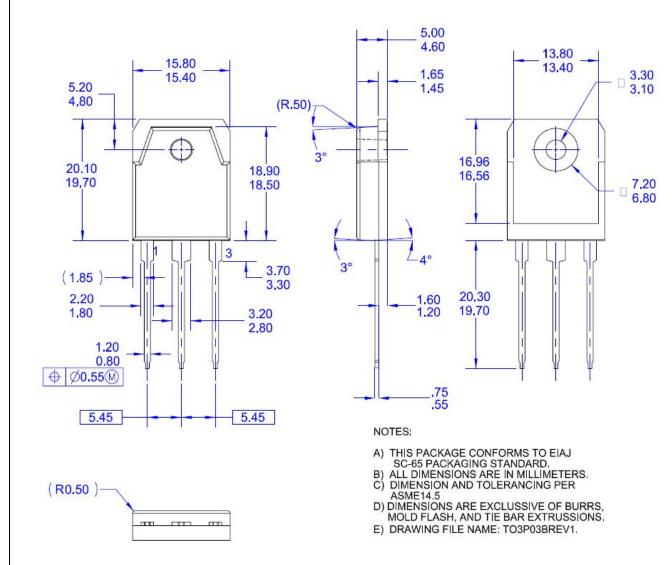


Figure 18. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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